ALPHA & OMEGA SEMICONDUCTOR

# AO4800B, AO4800BL
# Dual N-Channel Enhancement Mode Field Effect Transistor

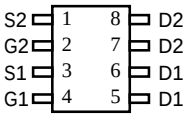
## General Description

The AO4800B/L uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in buck converters. *Standard Product AO4800B/L is Pb-free (meets ROHS & Sony 259 specifications).*

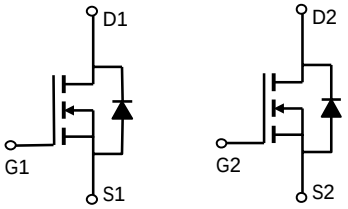
## Features

$V_{DS}$ (V) = 30V
$I_D$ = 6.9A ($V_{GS}$ = 10V)
$R_{DS(ON)}$ < 27mΩ ($V_{GS}$ = 10V)
$R_{DS(ON)}$ < 32mΩ ($V_{GS}$ = 4.5V)
$R_{DS(ON)}$ < 50mΩ ($V_{GS}$ = 2.5V)

***UIS TESTED!***
***Rg,Ciss,Coss,Crss Tested!***




**SOIC-8**




**Absolute Maximum Ratings $T_A$=25°C unless otherwise noted**

| Parameter | | Symbol | Maximum | Units |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±12 | V |
| Continuous Drain Current [AF] | $T_A$=25°C | $I_D$ | 6.9 | A |
| | $T_A$=70°C | | 5.8 | |
| Pulsed Drain Current [B] | | $I_{DM}$ | 40 | |
| Power Dissipation | $T_A$=25°C | $P_D$ | 1.9 | W |
| | $T_A$=70°C | | 1.2 | |
| Avalanche Current [B] | | $I_{AR}$ | 12 | A |
| Repetitive avalanche energy 0.3mH [B] | | $E_{AR}$ | 22 | mJ |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to 150 | °C |

**Thermal Characteristics**

| Parameter | | Symbol | Typ | Max | Units |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient [AF] | t ≤ 10s | $R_{\theta JA}$ | 55 | 62.5 | °C/W |
| Maximum Junction-to-Ambient [A] | Steady-State | | 90 | 110 | °C/W |
| Maximum Junction-to-Lead [C] | Steady-State | $R_{\theta JL}$ | 40 | 48 | °C/W |

**Electrical Characteristics ($T_J$=25°C unless otherwise noted)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **STATIC PARAMETERS** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $I_D$=250µA, $V_{GS}$=0V | 30 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$=24V, $V_{GS}$=0V | | 0.002 | 1 | µA |
| | | $T_J$=55°C | | | 5 | |
| $I_{GSS}$ | Gate-Body leakage current | $V_{DS}$=0V, $V_{GS}$= ±12V | | | 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$ $I_D$=250µA | 0.7 | 1 | 1.5 | V |
| $I_{D(ON)}$ | On state drain current | $V_{GS}$=4.5V, $V_{DS}$=5V | 40 | | | A |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}$=10V, $I_D$=6.9A | | 20 | 27 | mΩ |
| | | $T_J$=125°C | | 25 | 40 | |
| | | $V_{GS}$=4.5V, $I_D$=6A | | 23 | 32 | mΩ |
| | | $V_{GS}$=2.5V, $I_D$=5A | | 34 | 50 | mΩ |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$=5V, $I_D$=5A | 10 | 26 | | S |
| $V_{SD}$ | Diode Forward Voltage | $I_S$=1A,$V_{GS}$=0V | | 0.71 | 1 | V |
| $I_S$ | Maximum Body-Diode Continuous Current | | | | 4.5 | A |
| **DYNAMIC PARAMETERS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{GS}$=0V, $V_{DS}$=15V, f=1MHz | | 900 | 1100 | pF |
| $C_{oss}$ | Output Capacitance | | | 88 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 65 | | pF |
| $R_g$ | Gate resistance | $V_{GS}$=0V, $V_{DS}$=0V, f=1MHz | | 0.95 | 1.5 | Ω |
| **SWITCHING PARAMETERS** | | | | | | |
| $Q_g$ | Total Gate Charge | $V_{GS}$=4.5V, $V_{DS}$=15V, $I_D$=8.5A | | 10 | 12 | nC |
| $Q_{gs}$ | Gate Source Charge | | | 1.8 | | nC |
| $Q_{gd}$ | Gate Drain Charge | | | 3.75 | | nC |
| $t_{D(on)}$ | Turn-On DelayTime | $V_{GS}$=10V, $V_{DS}$=15V, $R_L$=1.8Ω, $R_{GEN}$=6Ω | | 3.2 | | ns |
| $t_r$ | Turn-On Rise Time | | | 3.5 | | ns |
| $t_{D(off)}$ | Turn-Off DelayTime | | | 21.5 | | ns |
| $t_f$ | Turn-Off Fall Time | | | 2.7 | | ns |
| $t_{rr}$ | Body Diode Reverse Recovery Time | $I_F$=5A, dI/dt=100A/µs | | 16.8 | 20 | ns |
| $Q_{rr}$ | Body Diode Reverse Recovery Charge | $I_F$=5A, dI/dt=100A/µs | | 8 | 12 | nC |

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in$^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A$=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in$^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A$=25°C. The SOA curve provides a single pulse rating.

Rev 1 : Dec 2007

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

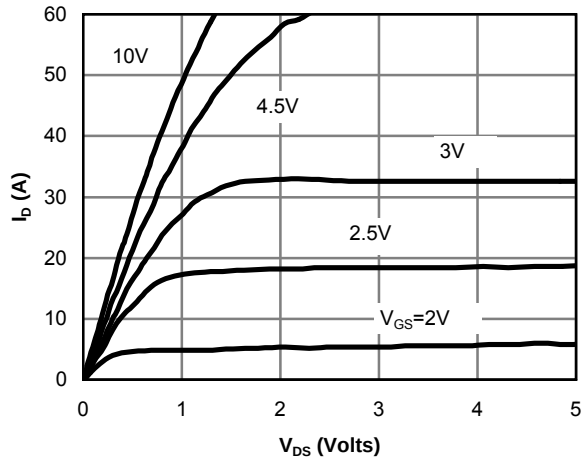



**Fig 1: On-Region Characteristics**

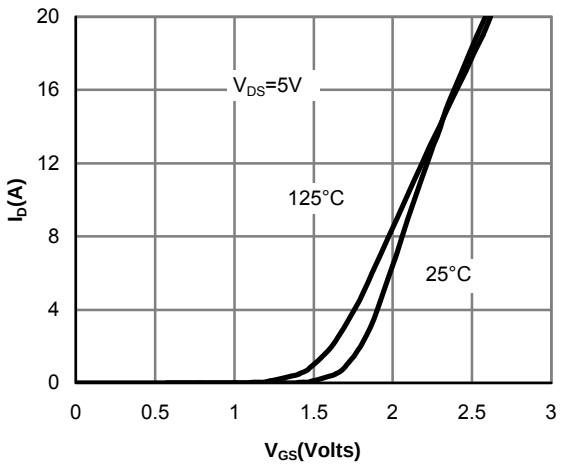



**Figure 2: Transfer Characteristics**

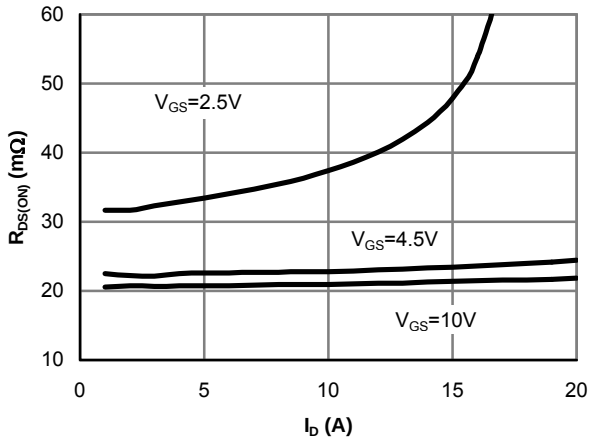



**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**

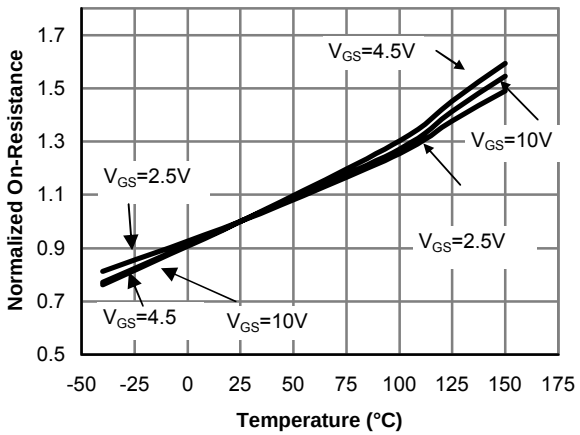



**Figure 4: On-Resistance vs. Junction Temperature**

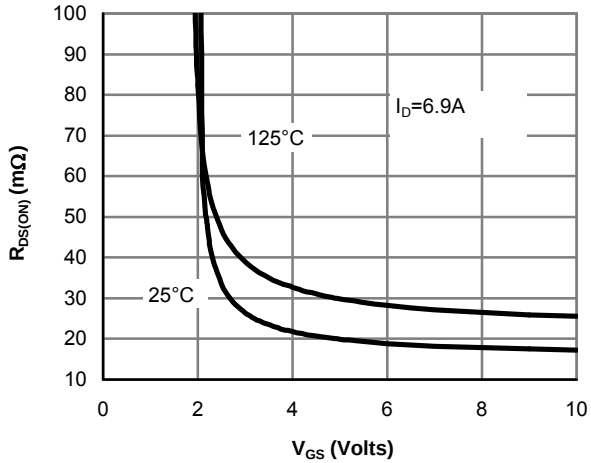



**Figure 5: On-Resistance vs. Gate-Source Voltage**

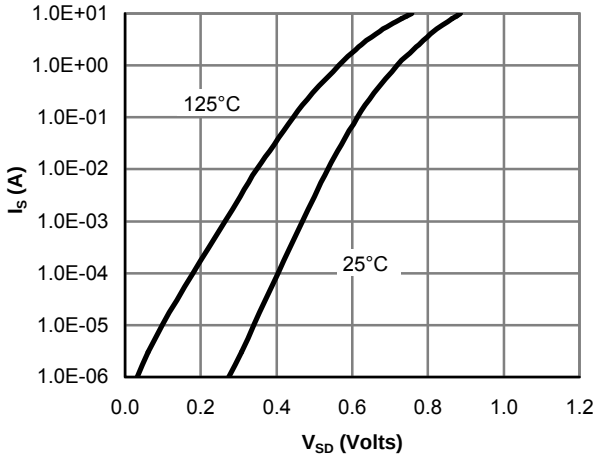



**Figure 6: Body-Diode Characteristics**

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

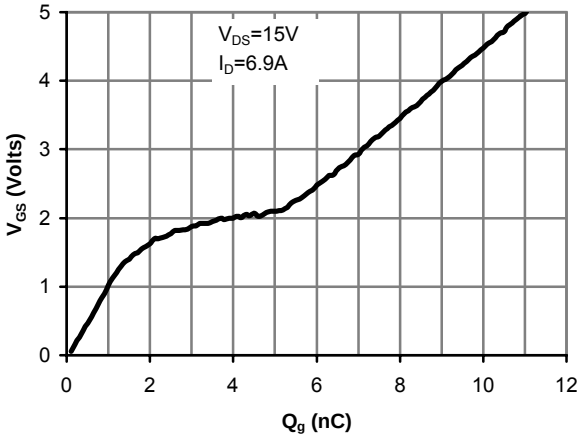



**Figure 7: Gate-Charge Characteristics**

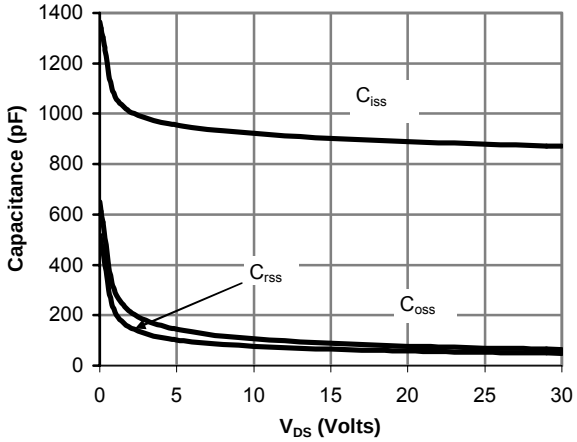



**Figure 8: Capacitance Characteristics**

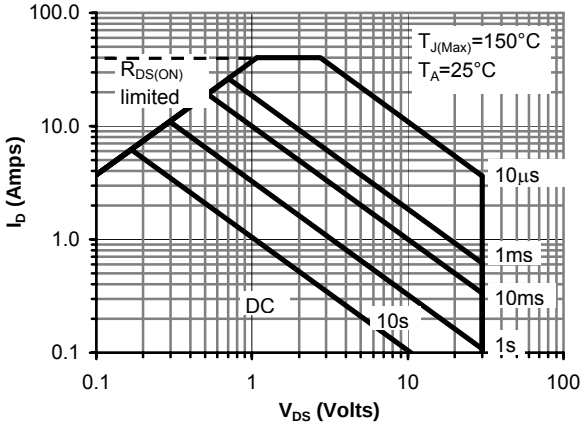



**Figure 9: Maximum Forward Biased Safe Operating Area (Note E)**

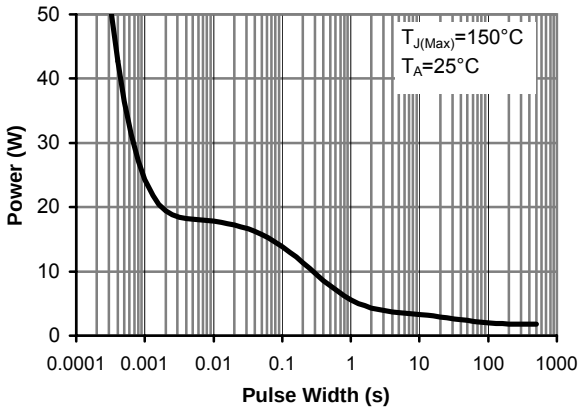



**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)**

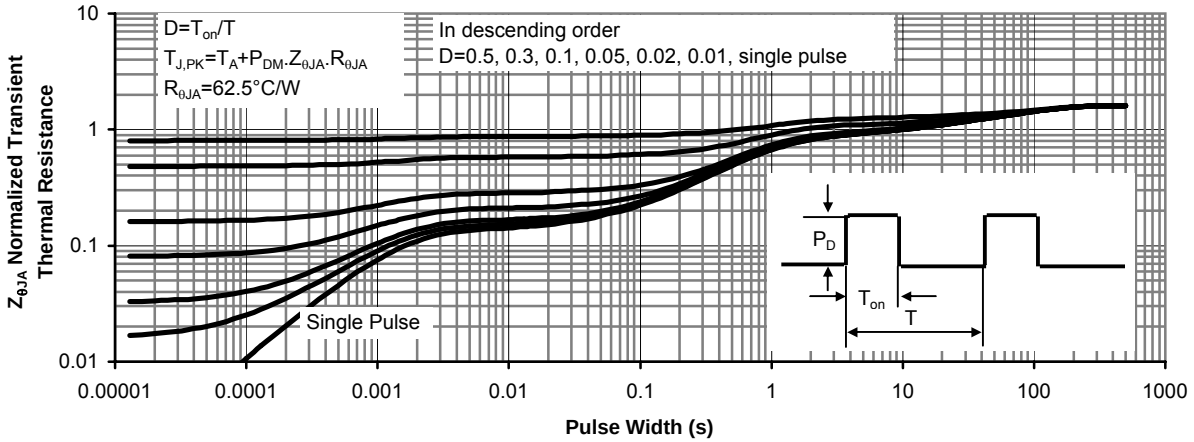



**Figure 11: Normalized Maximum Transient Thermal Impedance**